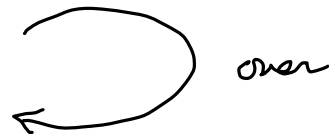


Lecture 11: Mechanics of Materials II

- Announcements:
- HW#2 online and due Tuesday, 2/28, at 10 a.m.
- -----
- Reading: Senturia, Chpt. 8
- Lecture Topics:
  - ↳ Stress, strain, etc., for isotropic materials
  - ↳ Thin films: thermal stress, residual stress, and stress gradients
  - ↳ Internal dissipation
  - ↳ MEMS material properties and performance metrics
- -----
- Last Time:
- Defined the linear thermal expansion coefficient
- Now, continue with this



Linear Thermal Expansion

temperature  $\uparrow$   $\rightarrow$  solids expand in volume

Definition: linear thermal expansion coefficient

$$\left. \begin{array}{l} \text{Linear Thermal} \\ \text{Exp. Coefficient} \end{array} \right\} \cong \alpha_T = \frac{d\epsilon_x}{dT} \quad [\text{Kelvin}^{-1}]$$

Remarks:

- ①  $\alpha_T$  values tend to be in the  $10^{-6}$  to  $10^{-7}$  range
- ②  $10^{-6} \text{K}^{-1} = 1 \mu\text{strain/K}$   $\rightarrow$
- ③ In 3D, get volume thermal exp. coefficient:

$$\frac{\Delta V}{V} = 3\alpha_T \Delta T$$

- ④ For moderate  $\Delta T$ 's  $\rightarrow \alpha_T \approx \text{constant}$   
 $\rightarrow$  for larger  $\Delta T$ , then  $\alpha_T = f(T)$

**Ex. Thin-film Thermal Stress**

Thin film ( $\alpha_{TF}$ )

Si Substrate ( $\alpha_{TS} = 2.8 \times 10^{-6} \text{ K}^{-1}$ )

Assume.

- Substrate is much thicker than the film.
- Film is deposited stress free @  $T_d$  ← deposition temperature
- The whole thing after deposition is cooled to room temperature,  $T_r$ .

Thermal strain of the substrate: (in one plane dimension)

$$\epsilon_s = -\alpha_{TS} \Delta T, \text{ where } \Delta T = T_d - T_r$$

If the film were not attached to the substrate:

$$\epsilon_{f, \text{free}} = -\alpha_{TF} \Delta T$$

But the film is attached to the substrate

↳ thickness of substrate  $\gg$  thickness of film  
∴ substrate wins!

↳ therefore the actual strain experienced by the film is that of the substrate:

$$\epsilon_{f, \text{attached}} = -\alpha_{TS} \Delta T$$

Thus:

Thermal Mismatch Strain:  $\epsilon_{f, \text{mismatch}} = (\alpha_{TF} - \alpha_{TS}) \Delta T$

↳ Note this is biaxial strain (assuming the film deposits isotropically onto the substrate)

$$\sigma_{f, \text{mismatch}} = \underbrace{\left( \frac{E}{1-\nu} \right)}_{E'} \epsilon_{f, \text{mismatch}}$$

Ex. Thin film is polyimide →  $\alpha_{TF} = 70 \times 10^{-6} \text{ K}^{-1}$ ,  $E' = 4 \text{ GPa}$   
deposited @  $250^\circ\text{C}$ , then cooled to  $RT = 25^\circ\text{C}$

$\Delta T = 225 \text{ K}$

$$\epsilon_{f, \text{mismatch}} = (70 - 2.8) \mu (225) = 1.5 \times 10^{-2}$$

↳ [ $\mu = 10^{-6}$ ,  $m = 10^{-3}$ ,  $k = 10^3$ ,  $G = 10^9$ ]

$$\sigma_{f, \text{mismatch}} = \underbrace{(4 \text{ G})}_{10^9} (1.5 \times 10^{-2}) = 60.5 \text{ MPa}$$

stress is (+) → tensile  
[(-) would be compressive]

SiO<sub>2</sub>